



Silicon Epitaxial Planar Diode

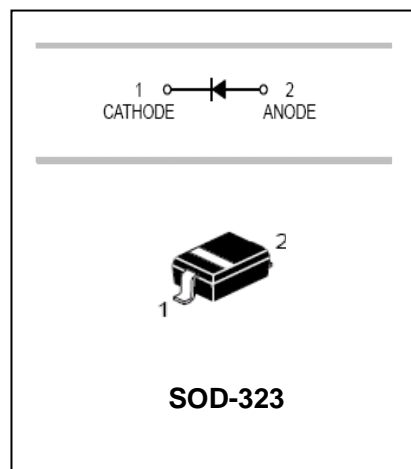
1SS352

FEATURES

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



Lead-free



APPLICATIONS

- High speed switching

ORDERING INFORMATION

Type No.	Marking	Package Code
1SS352	C1	SOD-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	85	V
DC Reverse Voltage	V_R	80	V
Average Rectified Output Current	I_O	100	mA
Surge current(10ms)	I_{FSM}	1	A
Power Dissipation	P_D	200	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{STG}	-55 to +125	°C

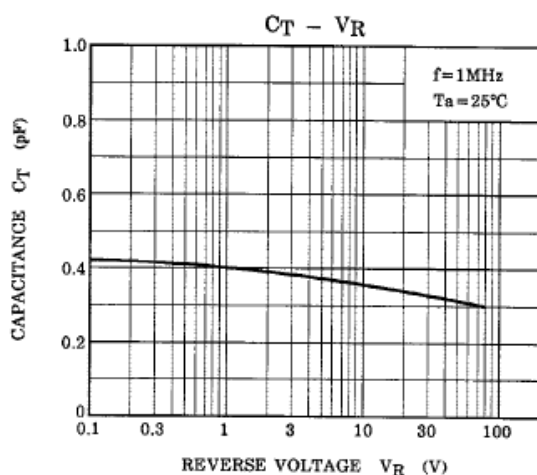
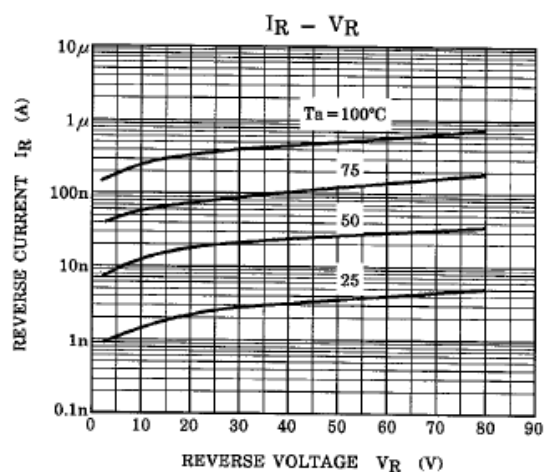
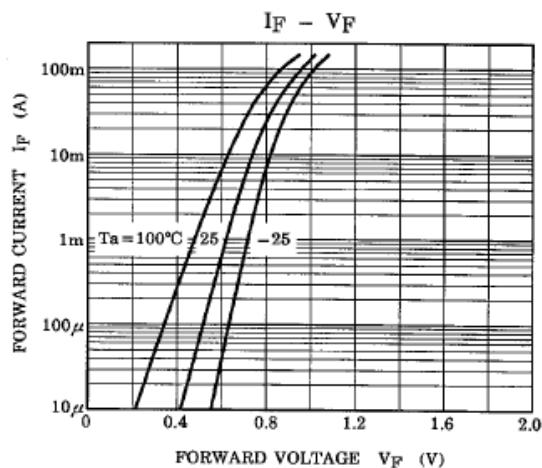
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

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Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=100\text{mA}$	- - -	0.62 0.75 0.98	- - 1.2	V
Reverse current	I_R	$V_R=30\text{V}$ $V_R=80\text{V}$	- -	- -	0.1 0.5	μA
Total Capacitance	C_T	$V_R=0, f=1\text{MHz}$		0.5	3.0	pF
Reverse recovery time	t_{rr}	$I_F=10\text{mA}$		1.6	4.0	ns

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



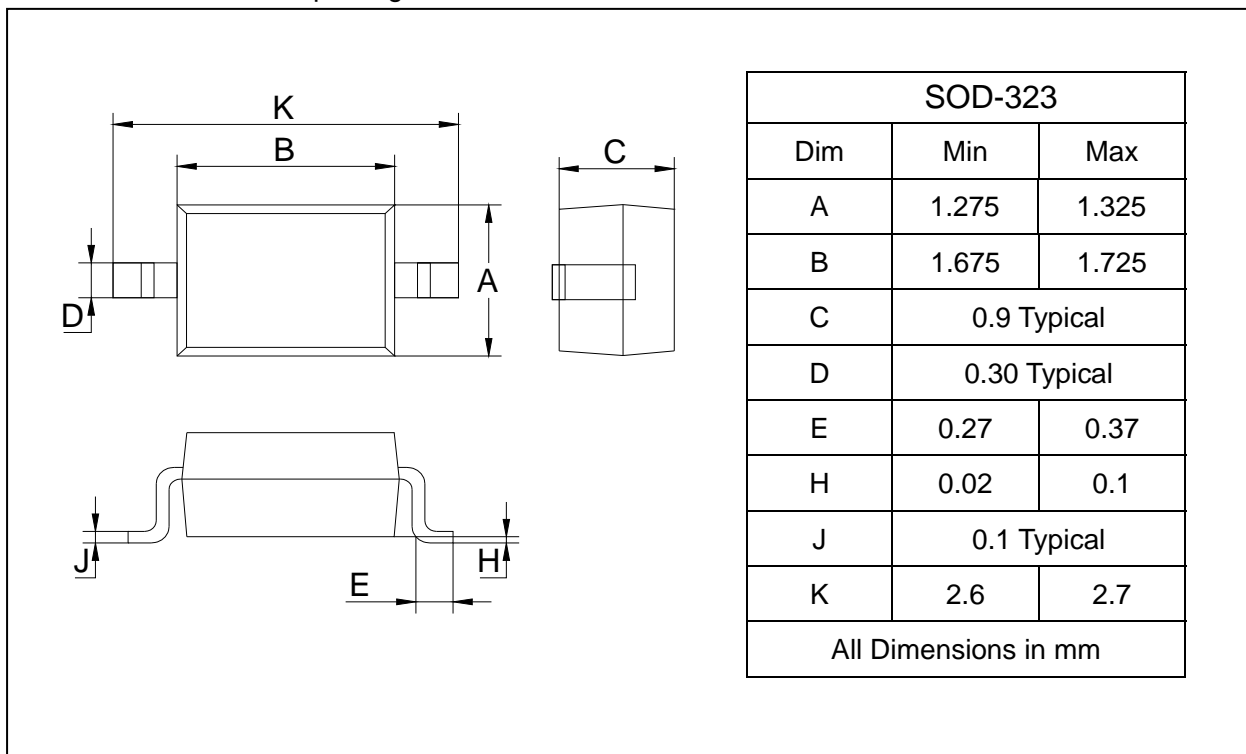
PACKAGE OUTLINE

Silicon Epitaxial Planar Diode

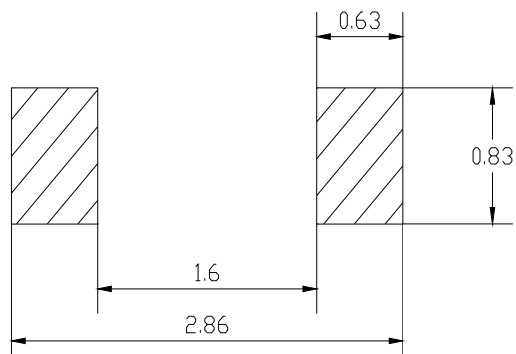
1SS352

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
1SS352	SOD-323	3000/Tape&Reel